IN THE SPECIFICATION:

Paragraph beginning at line 3 of page 1 has been amended as follows:

The present invention relates to a manufacturing method for a semiconductor device and, in particular, to a manufacturing method for a device having silicon oxide films with at least two different thicknesses, which includes a process for improving a reliability of the silicon oxide film.

Paragraph beginning at line 13 of page 1 has been amended as follows:

First, as shown in Fig. 2A, an element isolation film 10 is formed on a silicon semiconductor substrate 9 using any well-known technique. After that, a first gate oxide (insulating) film 11 is formed, for example, through thermal oxidation of the silicon substrate. Active regions are formed in two or more regions owing to the existence of the element isolation film 10.

Paragraph beginning at line 3 of page 2 has been amended as follows:

Subsequently, as shown in Fig. 2C, a mask member 13, which is used for opening at least a portion where a second

gate oxide film is to be formed, is made of, for example, a photoresist film using any well-known technique. Thereafter, a part of the first gate oxide film is selectively removed.

Paragraph beginning at line 3 of page 4 has been amended as follows:

Hereinafter, an embodiment of the present invention will be described with reference to Figs. 1A to 1E. First, as shown in Fig. 1A, an element isolation film 2 is formed on a silicon semiconductor substrate 1 using any well-known technique. After that, a first gate oxide film 3 having a first thickness is formed, for example, through thermal oxidation of the silicon substrate. Semiconductor active regions are formed in two or more regions apart from one another owing to existence of the element isolation film 2.

Paragraph beginning at line 17 of page 5 has been amended as follows:

Next, as shown in Fig. 1D, the mask member 5 is removed, followed by forming a second gate oxide film 6, for example, through the thermal oxidation of the silicon substrate 1. The second gate oxide film 6 has a second thickness different from the first thickness (e.g., in the embodiment of Figs. 1A-1E, the first thickness is greater than

the second thickness). At this time, no silicon oxynitride serving as an inhibitor against the oxidation remains on the silicon substrate surface on which the second gate oxide film is formed. Thus, the high-quality gate oxide film can be formed.

Paragraph beginning at line 20 of page 6 has been amended as follows:

According to the present invention, as set forth above, the silicon oxynitride formed after nitriding is removed from the portion where the second gate oxide film is formed and hence, no inhibition occurs against the oxidation upon the formation of the second gate oxide film, whereby the reliability of the second gate oxide film can be kept high.